

Amendments to the Abstract

Please delete the existing Abstract and substitute the following in its place:

B6

A method of forming a capacitor includes forming a first capacitor electrode over a substrate. A substantially crystalline capacitor dielectric layer is formed over the first capacitor electrode. The substrate with substantially crystalline capacitor dielectric layer is provided within a chemical vapor deposition reactor. A gaseous precursor comprising silicon is fed to the chemical vapor deposition reactor under conditions effective to substantially selectively deposit polysilicon on the substantially crystalline capacitor dielectric region, and the polysilicon is formed into a second capacitor electrode.